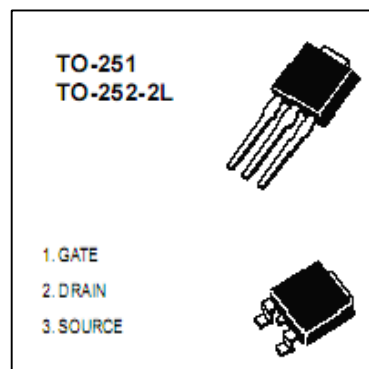
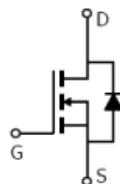


TO-252 Plastic-Encapsulate Transistors

4N60 MOSFET(N-Channel)

FEATURES

- Robust High Voltage Termination
- Avalanche Energy Specified
- Source-to-Drain Diode Recovery Time Comparable to a Discrete Fast Recovery Diode
- Diode is Characterized for Use in Bridge Circuits



MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Symbol (符号)	Parameter (参数名称)	Value (额定值)	Units (单位)
V _{DS}	Drain-Source voltage	600	V
V _{GS}	Gate-Source voltage	±30	V
I _D	Drain current-Continuous	4	A
P _D	Maximum Power Dissipation	2	W
E _{AS}	Single pulse avalanche energy	80	mJ
T _J ,T _{stg}	Operating Junction and Storage Temperature Range	-55-150	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250uA	600			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =600V, V _{GS} =0V			10	uA
Gate-body Leakage	I _{GSS}	V _{DS} =0V, V _{GS} =±30V			±100	nA
Gate-Threshold Voltage	V _{th(GS)}	V _{DS} = V _{GS} , I _D =250 uA	2		4	V
Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =2A			4	Ω
Diode Forward Voltage(Note3)	V _{SD}	V _{GS} =0V, I _D =4A			1.5	V
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f=1MHz		540		pF
Output Capacitance	C _{oss}			125		
Reverse Transfer Capacitance	C _{rss}			8.0		